



TO-92 Plastic-Encapsulate Transistors

2N6427 TRANSISTOR (NPN)

FEATURES

Power dissipation

$$P_{CM}: 0.350W \text{ (Tamb=25}^\circ\text{C)}$$

Collector current

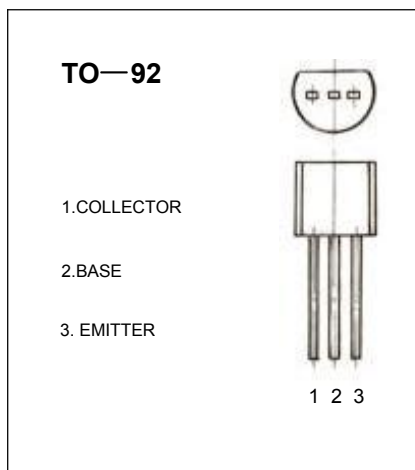
$$I_{CM}: 1.2 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO}: 40 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55^\circ\text{C to } +150^\circ\text{C}$$



ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10mA, I_B=0$	40			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	12			V
Collector cut-off current	I_{CEO}	$V_{CE}=25V, I_B=0$			1.0	μA
Collector cut-off current	I_{CBO}	$V_{CB}=30V, I_E=0$			50	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=10V, I_C=0mA$			50	μA
DC current gain	$H_{FE(2)}$	$V_{CE}=5V, I_C=10mA$	10K		100K	
DC current gain	$H_{FE(3)}$	$V_{CE}=5V, I_C=100mA$	20K		200K	
DC current gain	$H_{FE(4)}$	$V_{CE}=5V, I_C=500mA$	14K		140K	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=50mA, I_B=0.5mA$			1.2	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500mA, I_B=0.5mA$			1.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=500mA, I_B=0.5mA$			2.0	V
Base-emitter voltage	V_{BE}	$V_{CE}=5mA, I_C=50mA$			1.75	V

CLASSIFICATION OF HFE

Rank	1	2	3
Range	10K-100K	100K-150K	150K-200